FAIRCHILD
SEMICONDUCTOR TM

May 1994

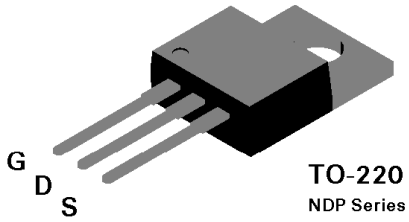
NDP408A / NDP408AE / NDP408B / NDP408BE
NDB408A / NDB408AE / NDB408B / NDB408BE
N-Channel Enhancement Mode Field Effect Transistor

General Description

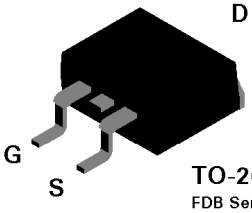
These N-channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulses in the avalanche and commutation modes. These devices are particularly suited for low voltage applications such as automotive, DC/DC converters, PWM motor controls, and other battery powered circuits where fast switching, low in-line power loss, and resistance to transients are needed.

Features

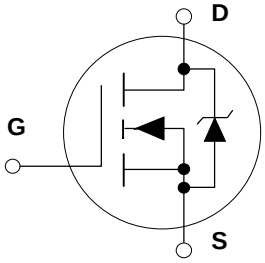
- 12 and 11A, 80V. $R_{DS(ON)}$ = 0.16 and 0.20Ω.
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- 175°C maximum junction temperature rating.
- High density cell design (3 million/in²) for extremely low $R_{DS(ON)}$.
- TO-220 and TO-263 (D^2PAK) package for both through hole and surface mount applications.



TO-220
NDP Series



TO-263AB
FDB Series



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter	NDP408A NDP408AE NDB408A NDB408AE	NDP408B NDP408BE NDB408B NDB408BE	Units
V_{DSS}	Drain-Source Voltage	80		V
V_{DGR}	Drain-Gate Voltage ($R_{GS} \leq 1$ MΩ)	80		V
V_{GSS}	Gate-Source Voltage - Continuous	±20		V
	- Nonrepetitive ($t_P < 50$ µs)	±40		V
I_D	Drain Current - Continuous	12	11	A
	- Pulsed	36	33	A
P_D	Total Power Dissipation @ T_C = 25°C	50		W
	Derate above 25°C	0.33		W/°C
T_J,T_{STG}	Operating and Storage Temperature Range	-65 to 175		°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	275		°C

Electrical Characteristics (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Type	Min	Typ	Max	Units
DRAIN-SOURCE AVALANCHE RATINGS (Note 1)							
E_{AS}	Single Pulse Drain-Source Avalanche Energy	V_{DD} = 25 V, I_D = 12 A	NDP408AE NDP408BE			40	mJ
I_{AR}	Maximum Drain-Source Avalanche Current		NDB408AE NDB408BE			12	A
OFF CHARACTERISTICS							
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 µA	ALL	80			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 80 V, V_{GS} = 0 V	ALL			250	µA
		T_J = 125°C				1	mA
I_{GSSF}	Gate - Body Leakage, Forward	V_{GS} = 20 V, V_{DS} = 0 V	ALL			100	nA
I_{GSSR}	Gate - Body Leakage, Reverse	V_{GS} = -20 V, V_{DS} = 0 V	ALL			-100	nA
ON CHARACTERISTICS (Note 2)							
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 µA	ALL	2	2.9	4	V
		T_J = 125°C		1.4	2.3	3.6	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 6 A	NDP408A NDP408AE NDB408A		0.11	0.16	Ω
		T_J = 125°C	NDB408AE		0.19	0.32	Ω
		V_{GS} = 10 V, I_D = 5.5 A	NDP408B NDP408BE NDB408B			0.2	Ω
		T_J = 125°C	NDB408BE			0.5	Ω
$I_{D(on)}$	On-State Drain Current	V_{GS} = 10 V, V_{DS} = 10 V	NDP408A NDP408AE NDB408A NDB408AE	11			A
			NDP408B NDP408BE NDB408B NDB408BE	10			A
g_{FS}	Forward Transconductance	V_{DS} = 10 V, I_D = 6 A	ALL	3	5.3		S
DYNAMIC CHARACTERISTICS							
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	ALL		380	500	pF
C_{oss}	Output Capacitance		ALL		115	125	pF
C_{rss}	Reverse Transfer Capacitance		ALL		35	50	pF

Electrical Characteristics (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Conditions	Type	Min	Typ	Max	Units
SWITCHING CHARACTERISTICS (Note 2)							
$t_{D(ON)}$	Turn - On Delay Time	V_{DD} = 40 V, I_D = 12 A, V_{GS} = 10 V, R_{GEN} = 24 Ω	ALL		7.5	20	nS
t_r	Turn - On Rise Time		ALL		48	80	nS
$t_{D(OFF)}$	Turn - Off Delay Time		ALL		22	40	nS
t_f	Turn - Off Fall Time		ALL		32	60	nS
Q_g	Total Gate Charge	V_{DS} = 64 V, I_D = 12 A, V_{GS} = 10V	ALL		12	17	nC
Q_{gs}	Gate-Source Charge		ALL		2.5		nC
Q_{gd}	Gate-Drain Charge		ALL		6		nC
DRAIN-SOURCE DIODE CHARACTERISTICS							
I_S	Maximum Continuos Drain-Source Diode Forward Current		NDP408A NDP408AE NDB408A NDB408AE			12	A
			NDP408B NDP408BE NDB408B NDB408BE			11	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		NDP408A NDP408AE NDB408A NDB408AE			36	A
			NDP408B NDP408BE NDB408B NDB408BE			33	A
V_{SD} (Note 2)	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 6 A	ALL		0.87	1.3	V
		T_J = 125°C			0.74	1.2	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 12 A, dI_S/dt = 100 A/µs	ALL		68	100	ns
I_{rr}	Reverse Recovery Current		ALL		4.7	7	A
THERMAL CHARACTERISTICS							
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		ALL			3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		ALL			62.5	°C/W

Notes:
1. NDP408A/408B and NDB408A/408B are not rated for operation in avalanche mode.
2. Pulse Test: Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0%.

Typical Electrical Characteristics

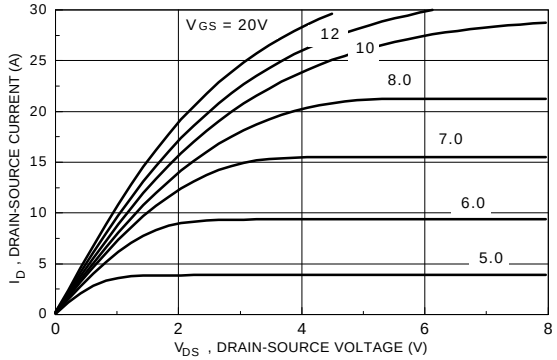


Figure 1. On-Region Characteristics.

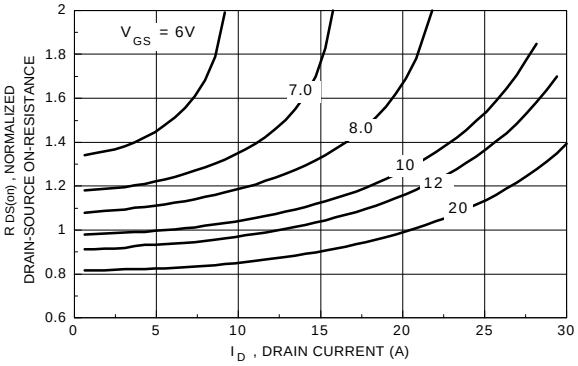


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.

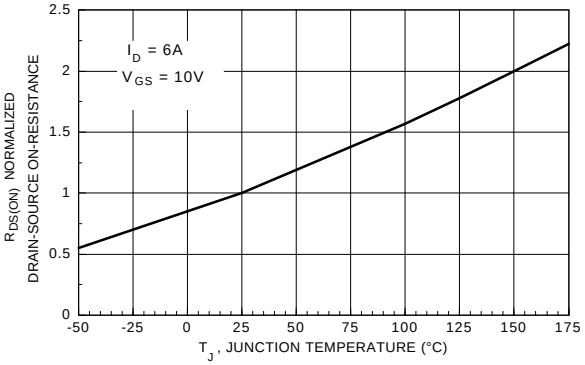


Figure 3. On-Resistance Variation with Temperature.

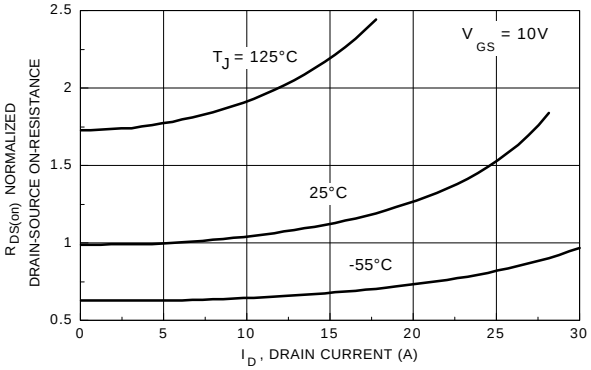


Figure 4. On-Resistance Variation with Drain Current and Temperature.

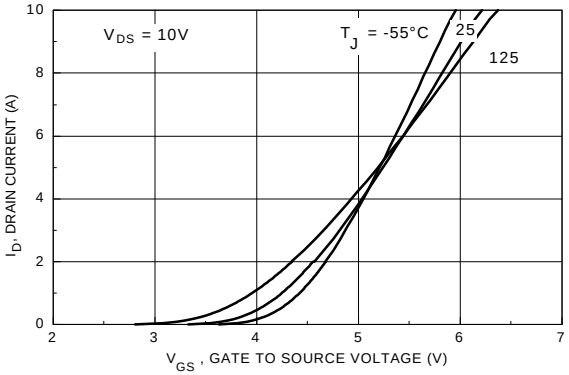


Figure 5. Transfer Characteristics.

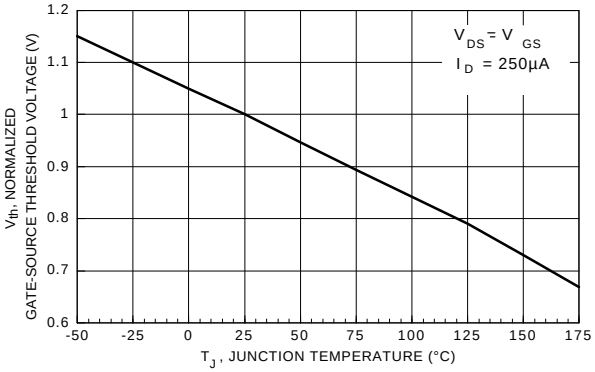


Figure 6. Gate Threshold Variation with Temperature.

Typical Electrical Characteristics (continued)

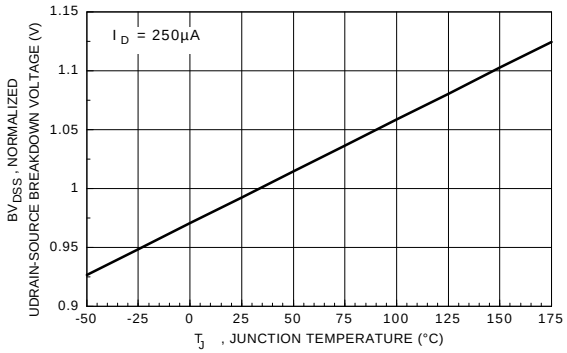


Figure 7. Breakdown Voltage Variation with Temperature.

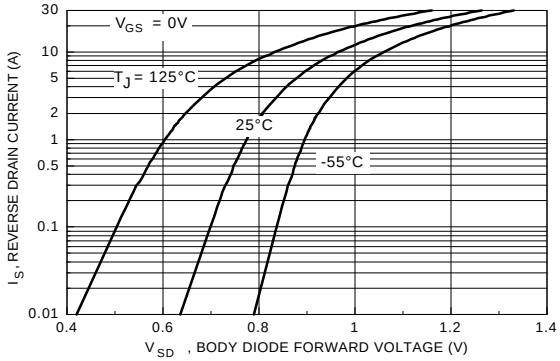


Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.

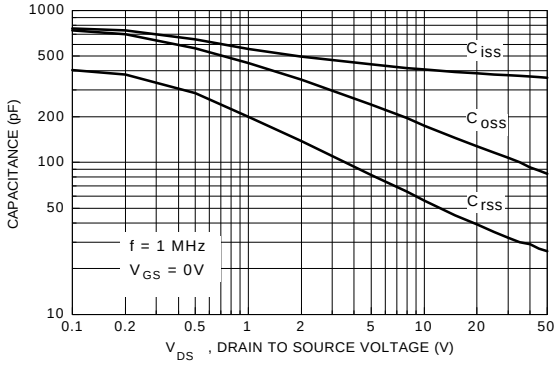


Figure 9. Capacitance Characteristics.

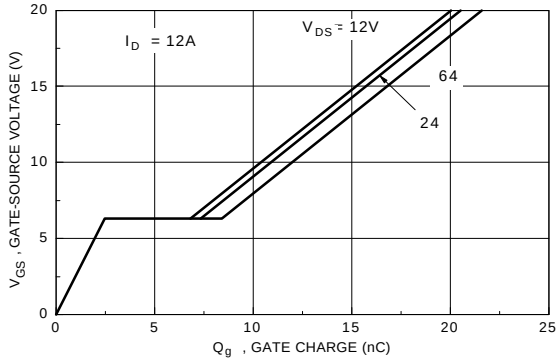


Figure 10. Gate Charge Characteristics.

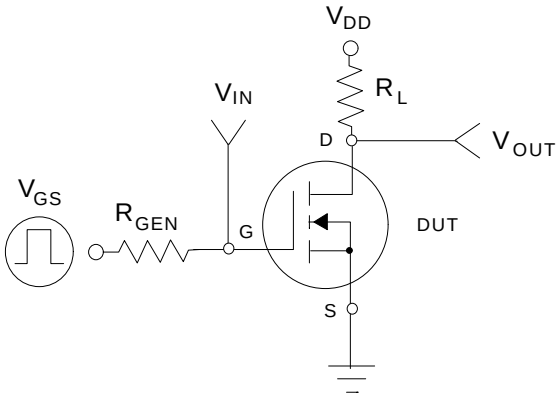


Figure 11. Switching Test Circuit.

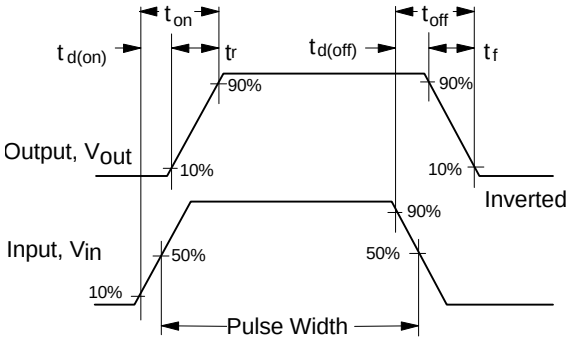


Figure 12. Switching Waveforms.

Typical Electrical Characteristics (continued)

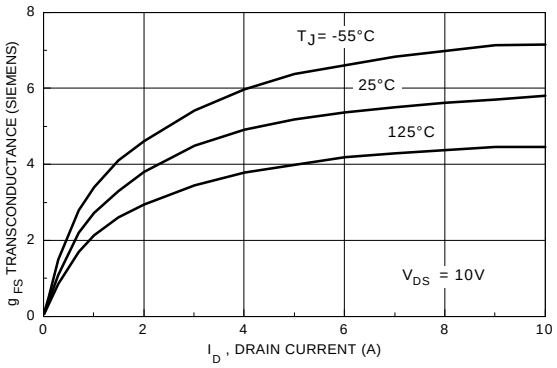


Figure 13. Transconductance Variation with Drain Current and Temperature.

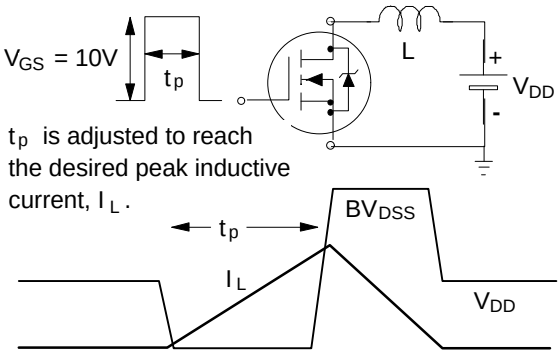


Figure 14. Unclamped Inductive Load Circuit and Waveforms.

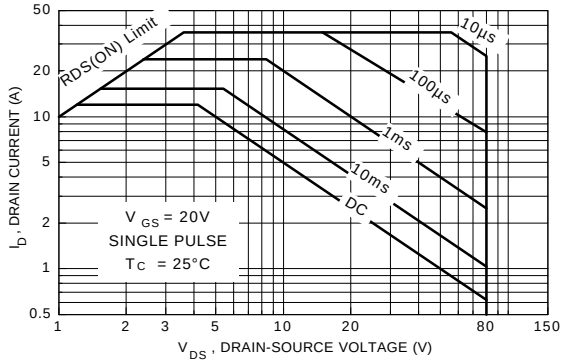


Figure 15. Maximum Safe Operating Area.

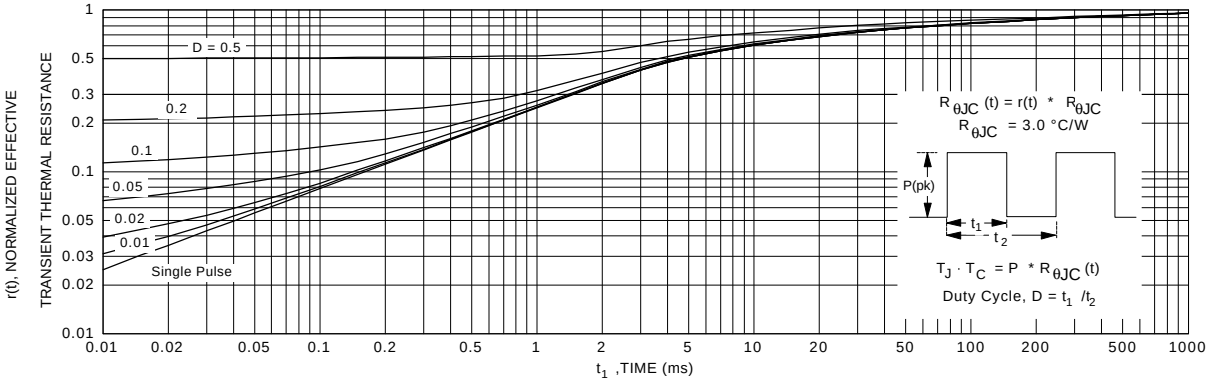


Figure 16. Transient Thermal Response Curve.

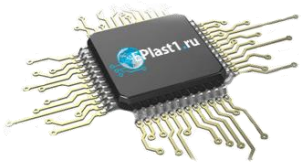
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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